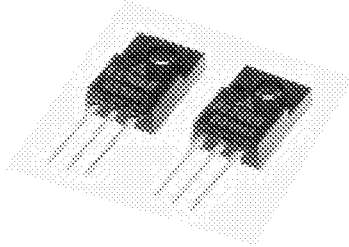


FS70KM-03

HIGH-SPEED SWITCHING USE

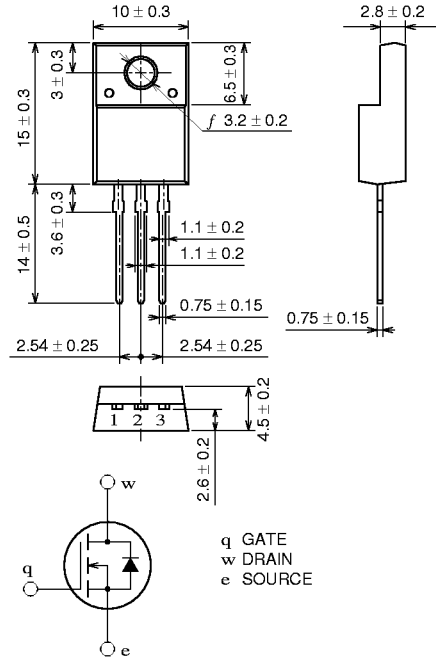
FS70KM-03



- ˆ 10V DRIVE
- ˆ V_{DSS} 30V
- ˆ r_{DS} (ON) (MAX) 14mΩ
- ˆ I_D 70A
- ˆ Integrated Fast Recovery Diode (TYP.) 70ns
- ˆ V_{iso} 2000V

OUTLINE DRAWING

Dimensions in mm



TO-220FN

APPLICATION

Motor control, Lamp control, Solenoid control
DC-DC converter, etc.

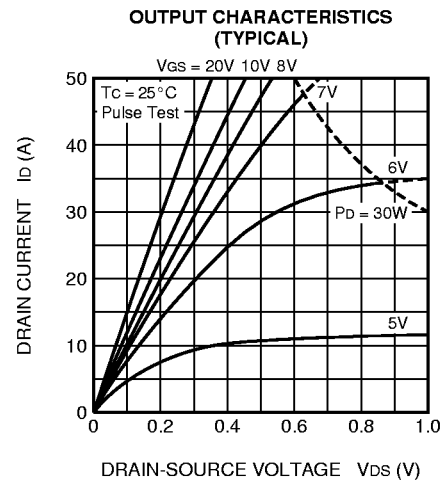
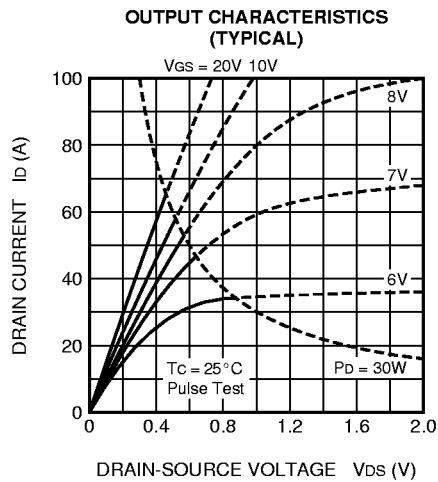
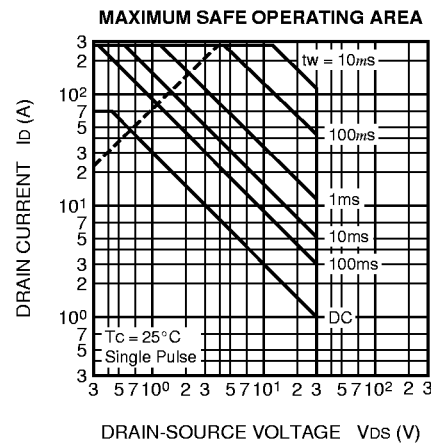
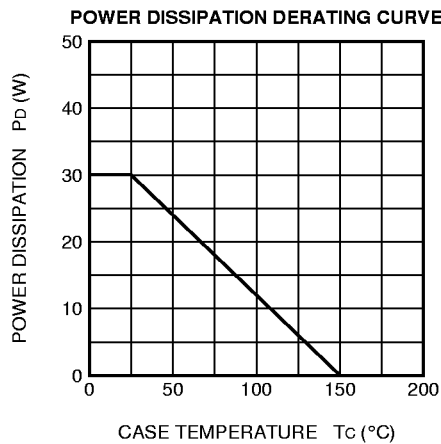
MAXIMUM RATINGS (T_C = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V _{DSS}	Drain-source voltage	V _{GS} = 0V	30	V
V _{GSS}	Gate-source voltage	V _{DS} = 0V	±20	V
I _D	Drain current		70	A
I _{DM}	Drain current (Pulsed)		280	A
I _{DA}	Avalanche drain current (Pulsed)	L = 30μH	70	A
I _S	Source current		70	A
I _{SM}	Source current (Pulsed)		280	A
P _D	Maximum power dissipation		30	W
T _{ch}	Channel temperature		-55 ~ +150	°C
T _{stg}	Storage temperature		-55 ~ +150	°C
V _{iso}	Isolation voltage	AC for 1minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g

ELECTRICAL CHARACTERISTICS ($T_{ch} = 25^{\circ}\text{C}$)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{mA}$, $V_{GS} = 0\text{V}$	30	—	—	V
I_{GSS}	Gate-source leakage current	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$	—	—	± 0.1	μA
I_{DSS}	Drain-source leakage current	$V_{DS} = 30\text{V}$, $V_{GS} = 0\text{V}$	—	—	0.1	mA
$V_{GS(th)}$	Gate-source threshold voltage	$I_D = 1\text{mA}$, $V_{DS} = 10\text{V}$	2.0	3.0	4.0	V
$r_{DS(on)}$	Drain-source on-state resistance	$I_D = 35\text{A}$, $V_{GS} = 10\text{V}$	—	11	14	$\text{m}\Omega$
$V_{DS(on)}$	Drain-source on-state voltage	$I_D = 35\text{A}$, $V_{GS} = 10\text{V}$	—	0.385	0.49	V
$ y_{fs} $	Forward transfer admittance	$I_D = 35\text{A}$, $V_{DS} = 10\text{V}$	—	36	—	S
C_{iss}	Input capacitance	$V_{DS} = 10\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	—	2400	—	pF
C_{oss}	Output capacitance		—	800	—	pF
C_{rss}	Reverse transfer capacitance		—	420	—	pF
$t_d(\text{on})$	Turn-on delay time	$V_{DD} = 15\text{V}$, $I_D = 35\text{A}$, $V_{GS} = 10\text{V}$, $R_{GEN} = R_{GS} = 50\Omega$	—	35	—	ns
t_r	Rise time		—	170	—	ns
$t_d(\text{off})$	Turn-off delay time		—	100	—	ns
t_f	Fall time		—	120	—	ns
V_{SD}	Source-drain voltage	$I_S = 35\text{A}$, $V_{GS} = 0\text{V}$	—	1.0	1.5	V
$R_{th(ch-c)}$	Thermal resistance	Channel to case	—	—	4.17	$^{\circ}\text{C/W}$
t_{rr}	Reverse recovery time	$I_S = 35\text{A}$, $di/dt = -50\text{A}/\mu\text{s}$	—	70	—	ns

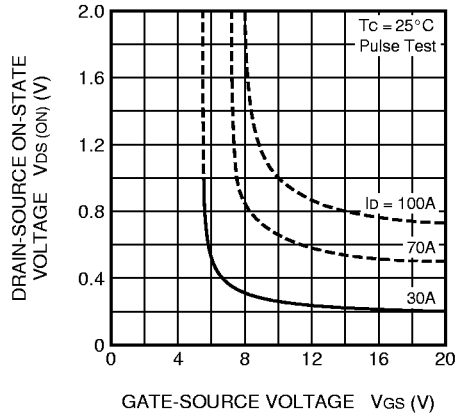
PERFORMANCE CURVES



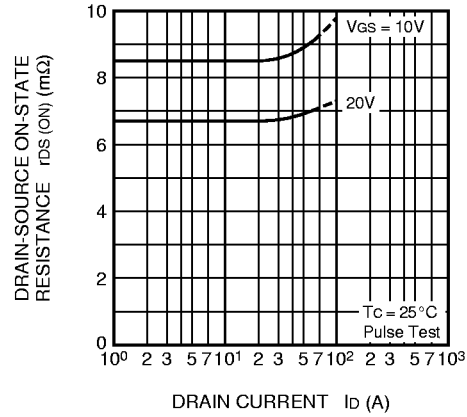
FS70KM-03

HIGH-SPEED SWITCHING USE

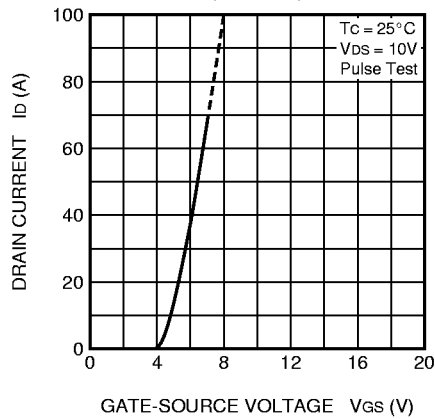
ON-STATE VOLTAGE VS.
GATE-SOURCE VOLTAGE
(TYPICAL)



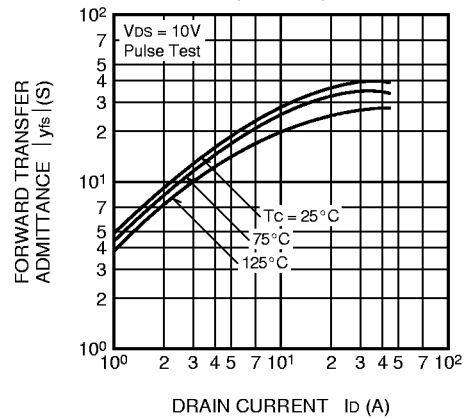
ON-STATE RESISTANCE VS.
DRAIN CURRENT
(TYPICAL)



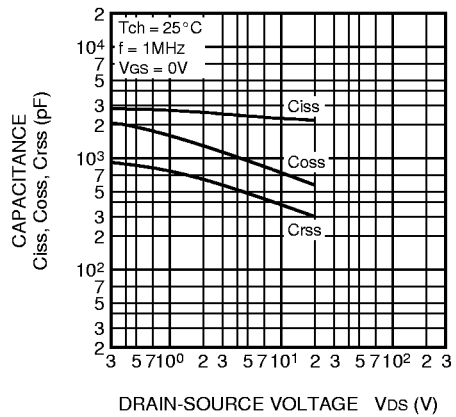
TRANSFER CHARACTERISTICS
(TYPICAL)



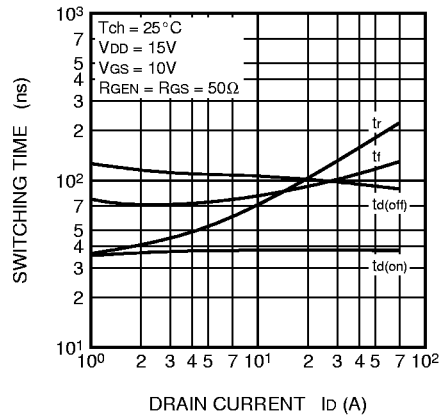
FORWARD TRANSFER ADMITTANCE
VS. DRAIN CURRENT
(TYPICAL)



CAPACITANCE VS.
DRAIN-SOURCE VOLTAGE
(TYPICAL)



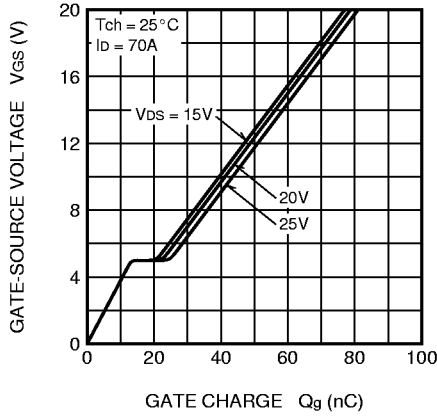
SWITCHING CHARACTERISTICS
(TYPICAL)



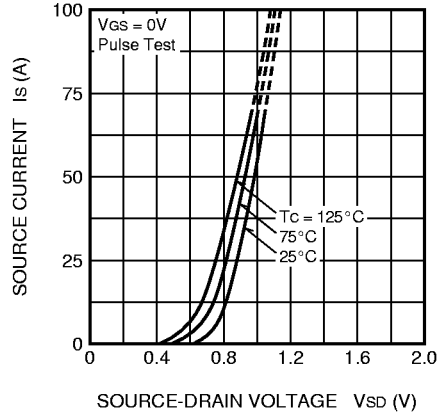
FS70KM-03

HIGH-SPEED SWITCHING USE

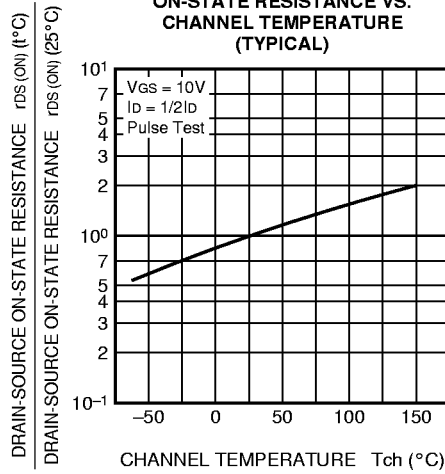
**GATE-SOURCE VOLTAGE
VS. GATE CHARGE
(TYPICAL)**



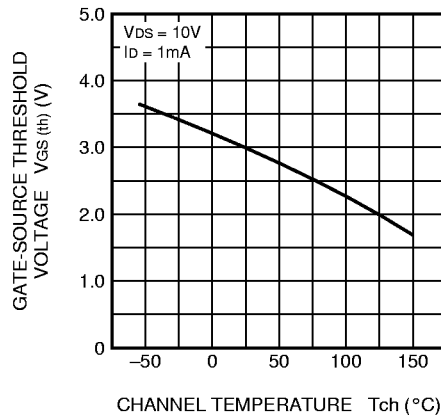
**SOURCE-DRAIN DIODE
FORWARD CHARACTERISTICS
(TYPICAL)**



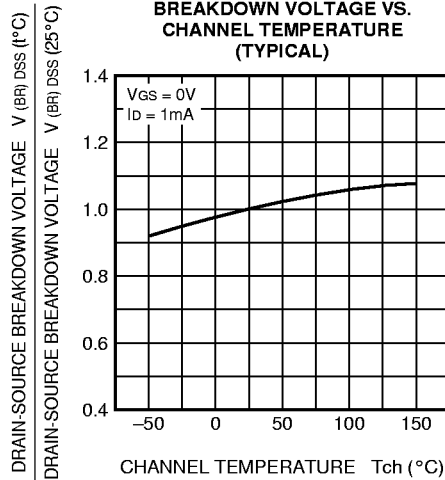
**ON-STATE RESISTANCE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**THRESHOLD VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**BREAKDOWN VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS**

